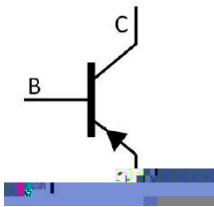


SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

High h_{FE} , low saturation voltage, complementary pair with KSC3265.

Low frequency power amplifier, power switching application.



PIN 1	Base	PIN 2	Emitter	PIN 3	Collector
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/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	O	Y
h _{FE} Range	100 200	160 320
Marking	HIO	HIY

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-30			V
Collector to Emitter Breakdown Voltage	V_{EBO}	$I_E=-1.0mA$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	100		320	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-800mA$	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-20mA$			-0.4	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-1.0V$ $I_C=-10mA$	-0.5		-0.8	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_C=-10mA$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$		13		pF

/ Electrical Characteristic Curve

